

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Vanhaelemeersh, et al.

) Group Art Unit 1763

Appl. No. : 09/530,069

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Filed : 07/03/2000

For : ANISOTROPIC ETCHING OF
ORGANIC-CONTAINING
INSULATING LAYERS) June 21, 2002
) (Date)
) *[Signature]*
) Rose M. Thiessen, Reg. No. 40,202

Examiner : Goudreau, G.

AMENDMENTUnited States Patent and Trademark Office
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Dear Sir:

In response to the Office Action mailed December 31, 2001 Applicants respectfully request that the Examiner enter the following amendments and consider the following remarks.

IN THE CLAIMS:

Please amend Claims 9 and 16 as follows:

9. (Twice Amended) A method for forming at least one opening in an organic-containing insulating layer comprising the step of:

covering said organic-containing insulating layer with a bilayer, said bilayer comprising a resist hard mask layer, being formed on said organic-containing insulating layer, and a resist layer being formed on said resist hard mask layer,

patterning said bilayer, and

creating said opening by plasma etching said organic-containing insulating layer in a reaction chamber containing a gaseous mixture, said gaseous mixture comprising an oxygen-